





20V PNP SILICON LOW SATURATION TRANSISTOR IN SOT23

Features and Benefits

- BV_{CEO} > -20V
- I_C = -1A Continuous Collector Current
- I_{CM} = -2A Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < -320 mV @ -1A$
- hFE characterised up to -1.5A for high current gain hold-up
- 500mW power dissipation
- Complementary part number FMMTL618
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- UL Flammability Rating 94V-0
- Case material: molded Plastic.
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Matte Tin Finish annealed over Copper plated Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

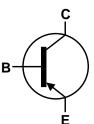
Applications

- MOSFET Gate Driving
- DC-DC Converters
- Charging circuit
- Power switches

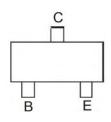
SOT23



Top View



Device Symbol



Top View Pin-Out

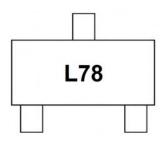
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMTL718TA	L78	7	8	3,000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com
- 3. For Packaging Details, go to our website at http://www.diodes.com.

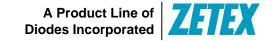
Marking Information



L78 = Product Type Marking Code

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Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-2	Α
Base Current	Ι _Β	-200	mA

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 4)	P_{D}	500	mW
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{ heta JA}$	250	°C/W
Thermal Resistance, Junction to Lead (Note 5)		$R_{ heta JL}$	197	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C	

Notes: 4. For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

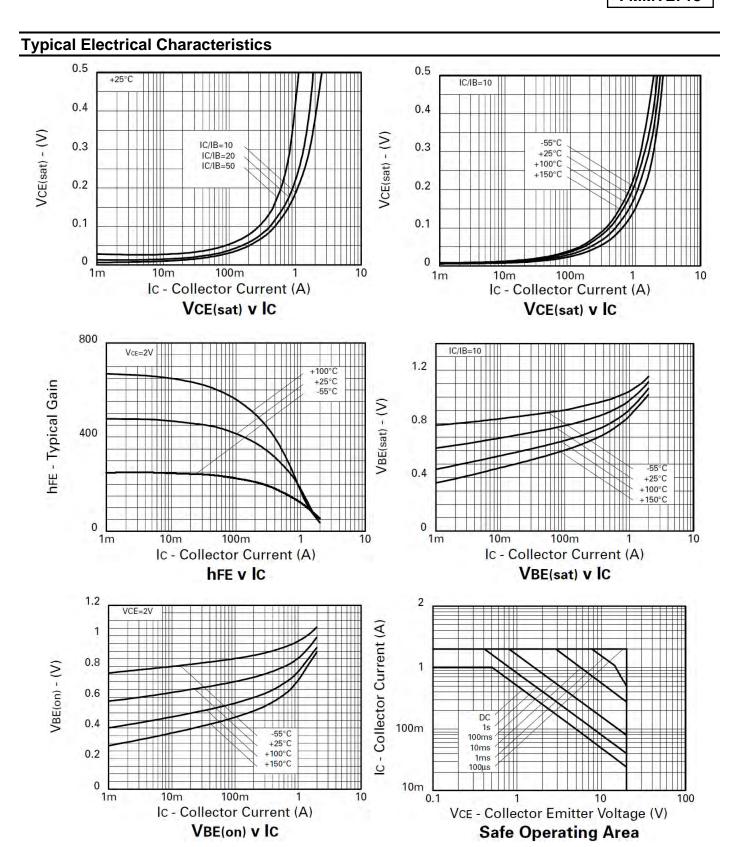
5. Thermal resistance from junction to solder-point (at the end of the collector lead).

Electrical Characteristics @TA = 25°C unless otherwise specified

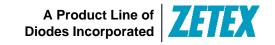
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-20	-65		V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	-20	-55		V	I _C = -10 mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	-8.8		V	I _E = -100 μA
Collector Cutoff Current	I _{CBO}			-10	nA	V _{CB} = -15V
Emitter Cutoff Current	I _{EBO}			-10	nA	$V_{EB} = -4V$
Collector Emitter Cutoff Current	I _{CES}			-10	nA	V _{CE} = -15V
Static Forward Current Transfer Ratio (Note 6)	h _{FE}	300 300 200 120 50	500 450 320 200 80			$\begin{split} I_C &= -10 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_C &= -100 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_C &= -0.5 \text{A}, \ V_{CE} = -2 \text{V} \\ I_C &= -1 \text{A}, \ V_{CE} = -2 \text{V} \\ I_C &= -1.5 \text{A}, \ V_{CE} = -2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 6)	VCE(sat)		-33 -130 -230 -315	-50 -180 -320 -450	mV mV mV	I_C =- 100mA, I_B = -10mA I_C =- 500mA, I_B = -20mA I_C =-1A, I_B = -50mA I_C =-1.5A, I_B = -100mA
Base-Emitter Turn-On Voltage(Note 6)	$V_{BE(on)}$		-0.85	-1.0	V	$I_C = -1.25A$, $V_{CE} = -2V$
Base-Emitter Saturation Voltage(Note 6)	V _{BE(sat)}		-0.95	-1.1	V	$I_C = -1.25A$, $I_B = -100mA$
Equivalent On-Resistance	R _{CE(sat)}		210		mΩ	$I_C = -1.5A$
Output Capacitance	C _{obo}		9	12	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T		265		MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz
Turn-On Time	t _{on}		108		ns	V _{CC} =-10V, I _C =-1A
Turn-Off Time	t _{off}		121		ns	$I_{B1} = I_{B2} = -10\text{mA}$

Note: 6. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

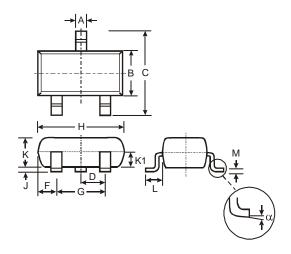






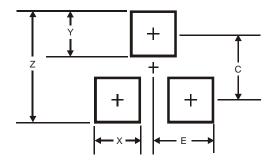


Package Outline Dimensions



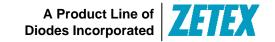
SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
C	2.0
ш	1.35





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